Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT78D (TO-220AB) internally insulated plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber. This device has high T_i operating capability and an internally isolated mounting base.

2. Features and benefits

- 3Q technology for improved noise immunity
- · High commutation capability with maximum false trigger immunity
- High surge capability
- High T_{i(max)}
- Isolated mounting base with 2500 V (RMS) isolation
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	140	A
Tj	junction temperature		-	-	150	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 116 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	12	A





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics	'				
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	50	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		sym051
3	G	gate		J
mb	n.c.	mounting base; isolated		
			TO-220AB (SOT78D)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BTA412Y-800B	TO-220AB	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220	SOT78D		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 116$ °C; Fig. 1; Fig. 2; Fig. 3	-	12	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	140	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	153	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	98	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

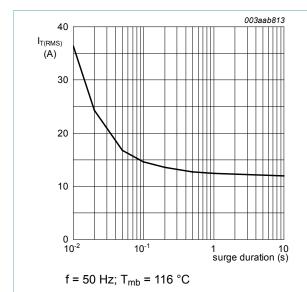


Fig. 1. RMS on-state current as a function of surge duration; maximum values

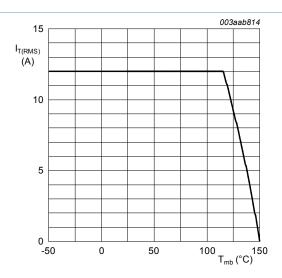


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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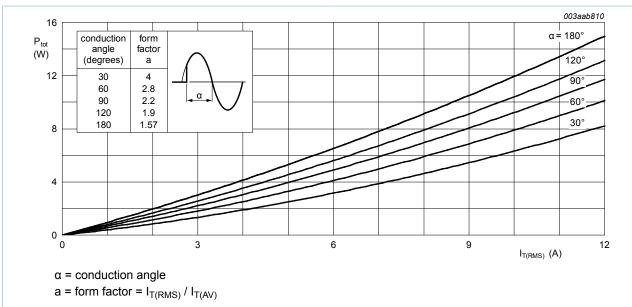


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

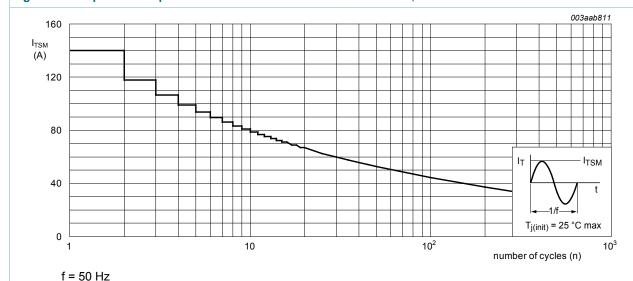
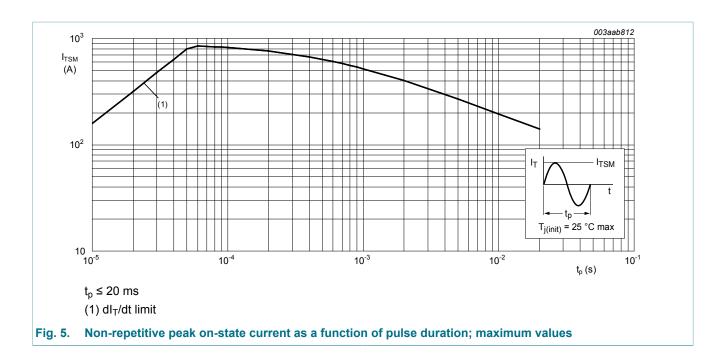


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	2.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

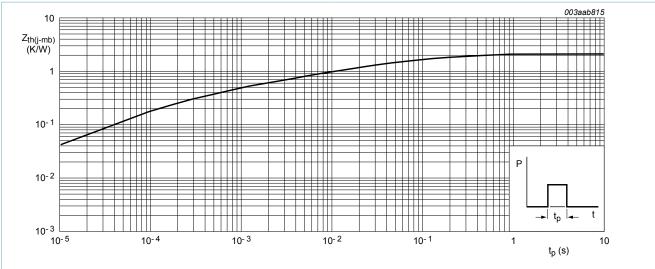


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T_{mb} = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _{mb} = 25 °C	-	10	-	pF

10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	50	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	8.0	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
		V _D = 800 V; T _j = 150 °C	-	0.4	2	mA
Dynamic	characteristics		'			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/µs
		V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	600	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	20	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	8	-	-	A/ms

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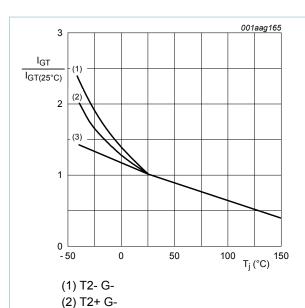


Fig. 7. Normalized gate trigger current as a function of junction temperature

(3) T2+ G+

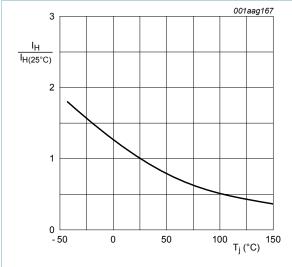


Fig. 9. Normalized holding current as a function of junction temperature

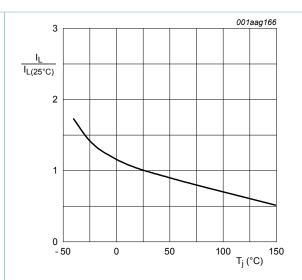
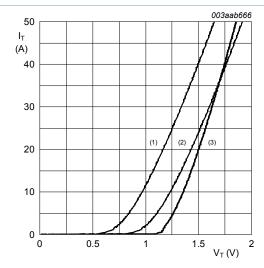


Fig. 8. Normalized latching current as a function of junction temperature



 $V_0 = 1.024 \text{ V}; R_s = 0.021 \Omega$

(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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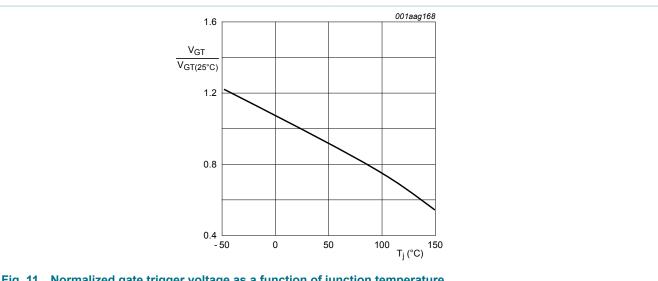
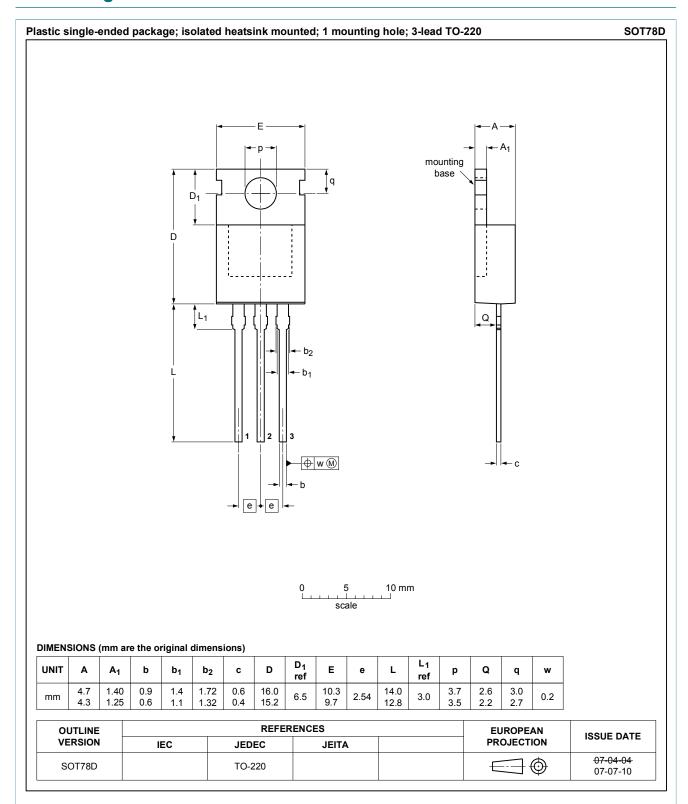


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline



12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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